

Research of Topics Discovery and Tech Evolution Based on Text Preprocessed Latent Dirichlet Allocation Model

Research Topic Analysis in GaN Tech Field

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Abstract—Computational Science and Data Science are inspiring the intelligent analysis and information service today. Machine learning text analysis is changing the traditional analysis methods. This article discusses the benefits of unsupervised learning approaches in patent text mining. Patent data of GaN industry were preprocessed by filter model based on NLTK Toolkit to identify the tech terms and then clustered them based on Latent Dirichlet Allocation model to find the latent topics which were visualized. Based on group operation, new emerging terms ranked by TFIDF through every year were used to reveal the research and development focused evolution. This research offers a demonstration of the proposed method based on 26,854 GaN patents. The results show 20 Research and Development topics with tech terms in GaN industry and present a Research and Development focus evolution based on new emerging terms every year, which provides a clue for more detailed analyses later. Our results show an efficient way to find technology focused evolution from a large scale text data.

Keywords- LDA; automatic term identification; preprocessed text; visualization.

I. INTRODUCTION

As an unsupervised learning method, the Latent Dirichlet Allocation (LDA) is widely used for topics finding in large text analysis. Topic model is a generative model for documents which are mixtures of topics comprising words over probability distribution. Traditionally, words were used to construct an LDA model, which resulted in quite a lot of general words on top of each topic. Herein, the noun terms are utilized instead of words to discover patterns of term-use and the documents relationship.

In the Derwent Innovation Index (DII) database, original patent titles and abstracts are rewritten in English and the technology details including patent novelty, use, advantage and so on from patent full text are extracted. In this paper, based on preprocessed text dataset of 26,854 patent titles and abstracts about GaN technology field from DII, the research topics were discovered, and R&D focus changes were detected and visualized.

Researches about R&D changes or evolution based on LDA have focuses at topic level. T. L.Griffiths et al. write about a method identifying 'hot topics' or 'cold topics' [1].

D. Choi et al. explore technological trends based on patent share and their change at the topic level [2]. X. C. Gong et al. detect topic splitting and merging based on the LDA Model [3]. J. B. Qu et al. analyze topic evolution with topic relevance from adjacent time intervals [4]. Many researches have improved and practiced methods detecting R&D changes or evolution at topic level, while few have discussed finer granularity analyzing at term level.

II. TEXT PREPROCESSING

Since most terms have the syntactic form of a noun phrase [5], identifying the noun phrases in the text was executed during text preprocessing. Part-Of-Speech Tagging in Python NLTK was used to construct language filter and identify noun phrases as following:

1. The sequence consists of nouns, v-ing form and adjectives, such as the phrase 'device comprising virtual display system'.
2. The sequence ends with a noun or a v-ing form, such as the phrase 'distributing workflow' or 'business computing'.

Additionally, stop contents were manipulated in the Python script from three different levels: sentence, phrase and word. For example, the publisher information sentence such as '(C) 2018 Elsevier B.V. All rights reserved' and the patent text description phrases such as 'independent claim' were stopped. Basically, uppercase and lowercase, singular and plural nouns and so on are preprocessed on word level.

After text preprocessing, the terms were prepared for LDA model.

III. RESEARCH TOPICS FINDING AND VISUALIZING

A. Research Topics Finding

The Gibbs sampling algorithm was used, with $\beta=0.1$, $\alpha=50/T$, (T is the number of topics) [6]. In practical application, β is relatively small and words can be expected into a specific research topic [1]. Since GaN field is already a specific area, fewer topics are involved in this case. Because the value of T in is very small, less than 30, topics for different T were discriminated manually to avoid overlap

between topics in macro level. Finally, 20 topics were suitable for GaN patent data, as shown in Table 1.

TABLE I. GaN RESEARCH TOPICS BASED ON LDA MODEL

| Topic1 | Score | Topic 2 | Score | Topic 3 | Score |
|----------------------------|--------|-----------------------------|--------|------------------------|--------|
| layer | 0.0919 | substrate | 0.0167 | gate electrode | 0.0258 |
| gallium | 0.0428 | material | 0.0097 | drain electrode | 0.0192 |
| buffer layer | 0.0399 | diode | 0.0077 | source electrode | 0.0177 |
| substrate | 0.0344 | array | 0.0066 | source | 0.0165 |
| aluminum | 0.0192 | device | 0.0061 | barrier layer | 0.0163 |
| Topic 4 | score | Topic 5 | score | Topic 6 | score |
| active layer | 0.0632 | substrate | 0.0676 | quantum dot | 0.0066 |
| light emitting device | 0.0241 | growing | 0.0161 | gallium arsenide | 0.0057 |
| emitting device | 0.0197 | layer | 0.0133 | indium | 0.0054 |
| semiconductor layer | 0.0167 | gallium | 0.0111 | composition | 0.0051 |
| p-type semiconductor layer | 0.0150 | epitaxial layer | 0.0105 | indium phosphide | 0.0049 |
| Topic 7 | score | Topic 8 | score | Topic 9 | score |
| substrate | 0.0185 | layer | 0.0188 | light | 0.0168 |
| temperature | 0.0162 | manufacture | 0.0165 | wavelength | 0.0104 |
| growing | 0.0115 | nitride semiconductor layer | 0.0148 | light source | 0.0074 |
| nitrogen | 0.0098 | group | 0.0107 | light-emitting device | 0.0071 |
| heating | 0.0089 | thickness | 0.0094 | phosphor | 0.0052 |
| Topic 10 | score | Topic 11 | score | Topic 12 | score |
| group | 0.0507 | forming | 0.0407 | aluminum | 0.0277 |
| crystal | 0.0205 | substrate | 0.0337 | silicon | 0.0245 |
| manufacture | 0.0192 | surface | 0.0180 | titanium | 0.0142 |
| gallium | 0.0140 | etching | 0.0152 | silicon carbide | 0.0138 |
| single crystal | 0.0108 | removing | 0.0099 | zinc | 0.0137 |
| Topic 13 | score | Topic 14 | score | Topic 15 | score |
| substrate | 0.0276 | device | 0.0216 | substrate | 0.0242 |
| active layer | 0.0111 | diode | 0.0095 | second electrode | 0.0104 |
| semiconductor laser | 0.0109 | semiconductor element | 0.0079 | material | 0.0102 |
| surface | 0.0105 | circuit | 0.0070 | first electrode | 0.0093 |
| direction | 0.0097 | anode | 0.0060 | electrode | 0.0092 |
| Topic 16 | score | Topic 17 | score | Topic 18 | score |
| substrate | 0.0405 | layer | 0.0515 | semiconductor layer | 0.0258 |
| surface | 0.0344 | chip | 0.0231 | light emitting element | 0.0189 |
| wafer | 0.0226 | p-type layer | 0.0164 | electrode | 0.0179 |
| gallium | 0.0200 | sapphire substrate | 0.0159 | light emitting diode | 0.0136 |
| laser beam | 0.0061 | n-type layer | 0.0148 | compound semiconductor | 0.0097 |

| Topic 19 | score | Topic 20 | score |
|---------------|--------|---------------|--------|
| substrate | 0.0370 | layer | 0.0258 |
| gallium | 0.0272 | active region | 0.0152 |
| manufacturing | 0.0263 | device | 0.0138 |
| surface | 0.0175 | first layer | 0.0138 |
| thin film | 0.0152 | second layer | 0.0120 |

B. Research Topics Visualization

Based on LDA model, the metric for terms and topics was measured and used to calculate the similarities between terms. A visualization map was constructed by applying Multidimensional Scaling to the similarities [6]. 20 topics in the GaN field were visualized, as shown in Figure 1. The threshold value for terms showed in the map was 0.001 in this case.

IV. R&D FOCUS EVOLUTING

The metric θ of topics and documents was used to find the topic contributing the most to every document. $\theta_{i,j}$ can reveal the degree to which topic i is referred to in the document j , (1). $p(\text{topic}=i | \theta)$ according to Dirichlet distribution ($\theta_{i,j} \geq 0, \sum_i \theta_{i,j} = 1$) [7]. The most contributed topic was assigned for every document in this case.

$$\theta_{m \times k} = \begin{bmatrix} \theta_{0,0} & \theta_{0,1} & \dots & \theta_{0,k} \\ \theta_{1,0} & \theta_{1,1} & \dots & \theta_{1,k} \\ \vdots & \vdots & \ddots & \vdots \\ \theta_{m,0} & \theta_{m,1} & \dots & \theta_{m,k} \end{bmatrix} \begin{matrix} \text{topic}_0 & \text{topic}_1 & \dots & \text{topic}_k \\ \text{doc}_0 \\ \text{doc}_1 \\ \vdots \\ \text{doc}_k \end{matrix} \quad (1)$$

The evolution of R&D focus through new terms emerging in every year was observed. All documents were grouped by year, and terms in a year's documents were counted. Terms_y means terms in year. Then, (2) was used to extract new emerging terms in year y , E_y , ranked by sum of TF-IDF scores.

$$E_y = \text{Terms}_y - \sum_{n=y_0}^{y-1} \text{Terms}_n. \quad (2)$$

In practice, the top technical terms are ranked and identified by term frequency and TF-IDF value. But there are a large number of high frequency general terms by term frequency rank while the technical terms obtained by TF-IDF are more meaningful. Based on (2), new emerging terms were counted from 2011 to 2017 every year in GaN field, as shown in Figure 2.

V. CONCLUSIONS AND FUTURE WORK

The analysis model proposed in this paper gives an efficient way to find technology focus evolution from a large scale text data, such as patent information in this case. Compared with topic level analysis, the tech evolution provides a breakthrough point for finer granularity analyzing to discover hot tech researches on a timescale which could be a clue for finding more information about these tech focuses. In the future, we will continue to optimize the analysis model in practice, especially the processing of synonyms.

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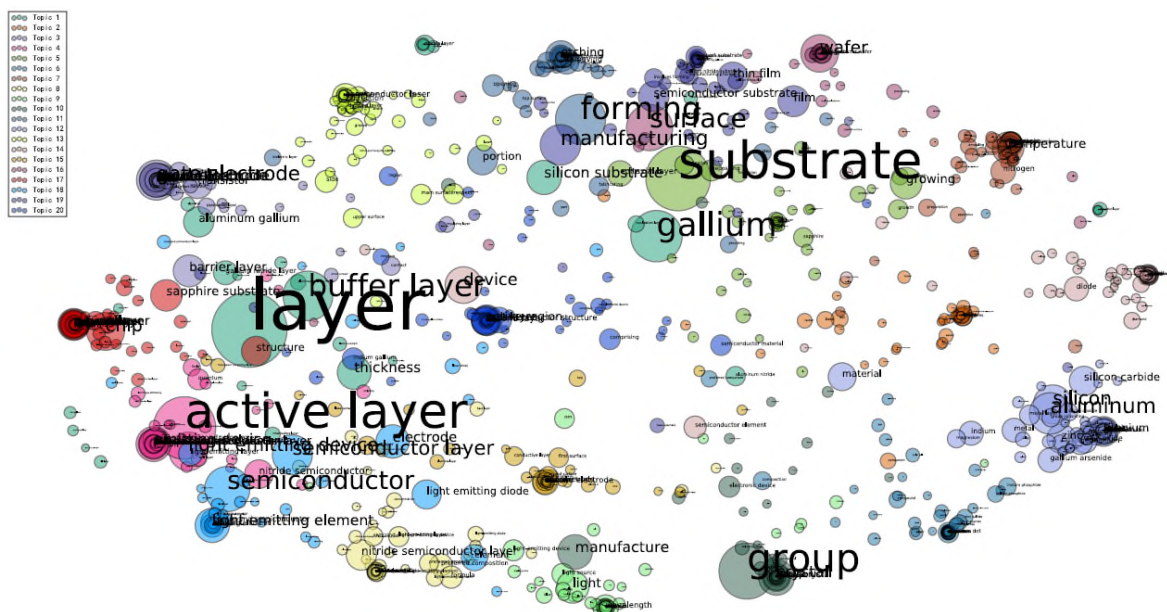


Figure 1. Visualization of GaN research topics

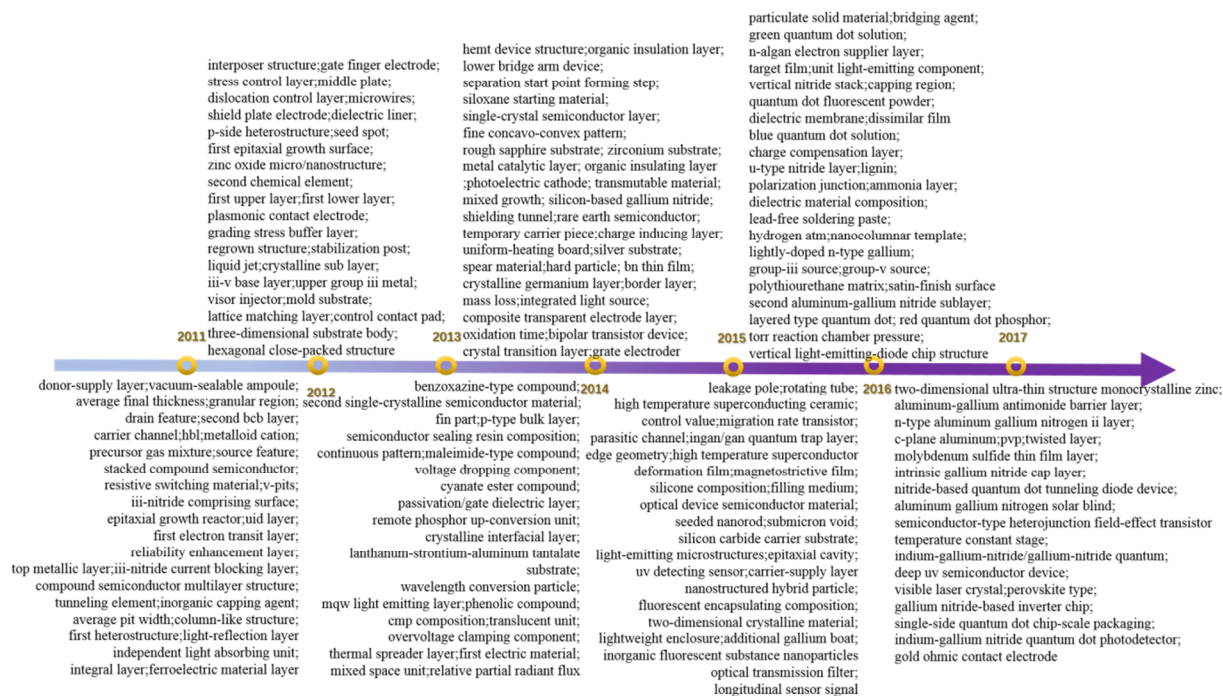


Figure 2. GaN Tech evolution based on new terms from 2011 to 2017